

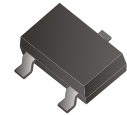
SMD Switching Diode



SMD Diodes Specialist

CDST116-G

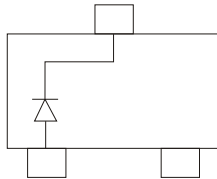
RoHS Device



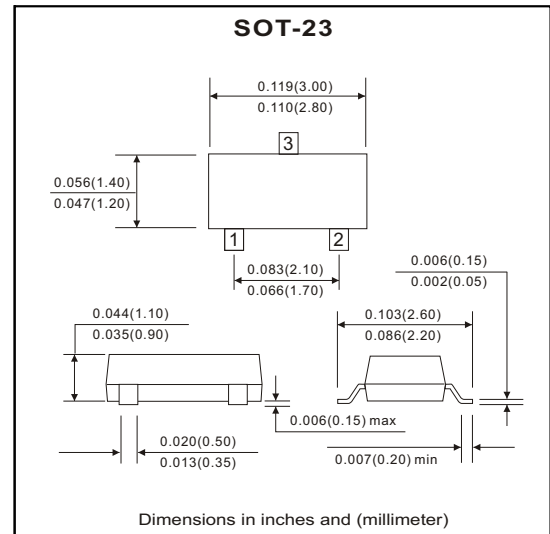
Features

- Low leakage current applications.
- Medium speed switching times.

Polarity:



Marking: JV



Maximum Ratings (at Ta=25°C unless otherwise noted)

| Parameter | Symbol | Value | Unit |
|---|---------------------------------|-------------|------|
| Peak repetitive peak reverse voltage Working peak reverse voltage DC blocking voltage | V_{RRM} V_{RWM} V_R | 75 | V |
| Forward continuous current | I_{FM} | 215 | mA |
| Power dissipation | P_D | 250 | mW |
| Junction temperature | T_J | 150 | °C |
| Storage temperature | T_{STG} | -55 to +150 | °C |

Electrical Characteristics (at Ta=25°C unless otherwise noted)

| Parameter | Conditions | Symbol | Min | Typ. | Max | Unit |
|-------------------------------|--|-------------|-----|------|------|---------|
| Reverse breakdown voltage | $I_R=100\mu A$ | $V_{(BR)R}$ | 75 | | | V |
| Forward voltage | $I_F=1mA$ | V_{F1} | | | 0.9 | V |
| | $I_F=10mA$ | V_{F2} | | | 1 | V |
| | $I_F=50mA$ | V_{F3} | | | 1.1 | V |
| | $I_F=150mA$ | V_{F4} | | | 1.25 | V |
| Reverse current | $V_R=75V$ | I_R | | | 5 | μA |
| Capacitance between terminals | $V_R=0V, f=1MHz$ | C_T | | 2 | | pF |
| Reverse recovery time | $I_F=I_R=10mA, I_{rr}=0.1 \times I_R, R_L=100\Omega$ | t_{rr} | | | 3 | nS |

RATING AND CHARACTERISTIC CURVES (CDST116-G)

Fig.1 Forward Current Derating Curve

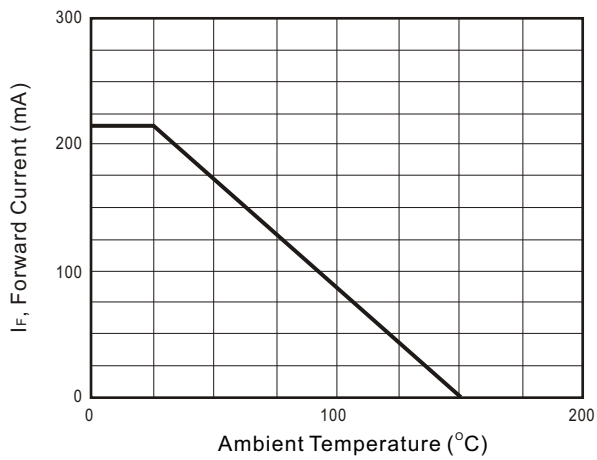


Fig.2 Forward Voltage Characteristics

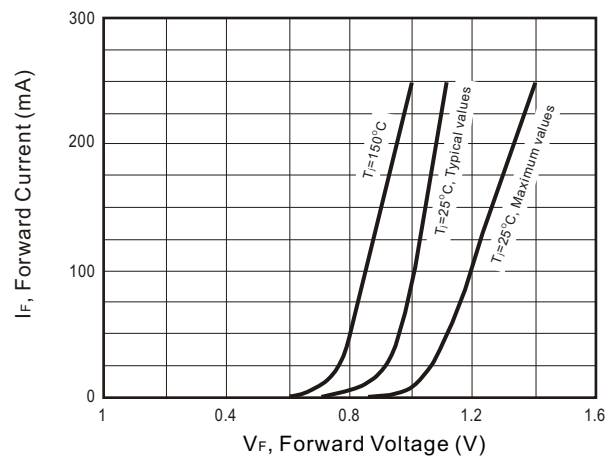


Fig.3 Reverse Characteristics

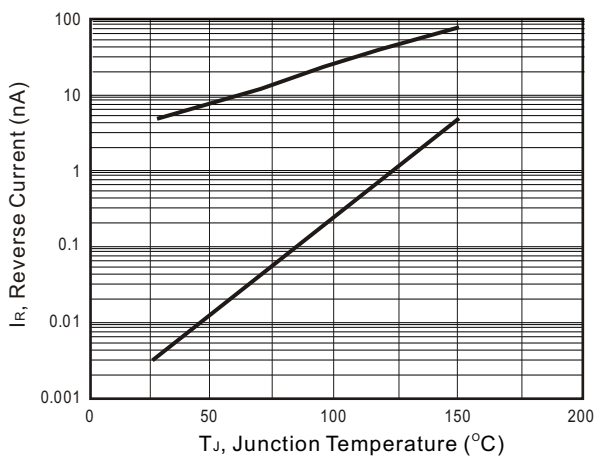


Fig.4 Diode Capacitance Characteristics

